

## SKiiP 3-phase bridge

Absolute Maximum Ratings		Values	Units
Symbol	Conditions <sup>1)</sup>		
$V_{isol}$ <sup>4)</sup>	AC, 1min	2500	V
$T_{op}, T_{stg}$	Operating / stor. temperature	-25...+85	°C
<b>IGBT and Inverse Diode</b>			
$V_{CES}$		600	V
$V_{CC}$ <sup>5)</sup>	Operating DC link voltage	400	V
$I_C$	IGBT	200	A
$T_j$ <sup>3)</sup>	IGBT + Diode	-40...+150	°C
$I_F$	Diode	200	A
$I_{FM}$	Diode, $t_p < 1$ ms	400	A
$I_{FSM}$	Diode, $T_j = 150$ °C, 10ms; sin	2000	A
$I^2t$ (Diode)	Diode, $T_j = 150$ °C, 10ms	20	kAs <sup>2</sup>
<b>Driver</b>			
$V_{S1}$	Stabilized Power Supply	18	V
$V_{S2}$	Non-stabilized Power Supply	30	V
$f_{smax}$	Switching frequency	20	kHz
$dV/dt$	Primary to secondary side	75	kV/μs

Characteristics		min.	typ.	max.	Units
Symbol	Conditions <sup>1)</sup>				
<b>IGBT <sup>11)</sup></b>					
$V_{(BR)CES}$	Driver without supply	$\geq V_{CES}$	–	–	V
$I_{CES}$	$V_{GE} = 0, T_j = 25$ °C	–	–	0,4	mA
	$V_{CE} = V_{CES}, T_j = 125$ °C	–	3	–	mA
$V_{TO}$	$T_j = 125$ °C	–	–	0,94	V
$r_T$	$T_j = 125$ °C	–	–	9,6	mΩ
$V_{Cesat}$	$I_C = 200A, T_j = 125$ °C	–	–	2,9	V
$V_{Cesat}$	$I_C = 200A, T_j = 25$ °C	–	–	2,65	V
$E_{on} + E_{off}$	$V_{CC}=300/400V, I_C=200A, T_j = 125$ °C	–	–	18/25	mJ
$C_{CHC}$	per SKiiP, AC side	–	0,8	–	nF
$L_{CE}$	Top, Bottom	–	15	–	nH
<b>Inverse Diode <sup>2)</sup></b>					
$V_F = V_{EC}$	$I_F = 200A, T_j = 125$ °C	–	–	1,72	V
$V_{F0} = V_{EC}$	$I_F = 200A, T_j = 25$ °C	–	–	1,75	V
$E_{on} + E_{off}$	$I_F = 200A, T_j = 125$ °C	–	–	6	mJ
$V_{TO}$	$T_j = 125$ °C	–	–	0,78	V
$r_T$	$T_j = 125$ °C	–	–	5,0	mΩ
<b>Thermal Characteristics</b>					
$R_{thjs}$ <sup>10)</sup>	per IGBT	–	–	0,225	K/W
$R_{thjs}$ <sup>10)</sup>	per Diode	–	–	0,375	K/W
$R_{thsa}$ <sup>6,10)</sup>	P16 heatsink; see case S5	–	–	36	K/KW
<b>Driver</b>					
$I_{S1}$	Supply current 15V-supply	$340+240 \cdot f_s / f_{smax} + 3,5 \cdot I_{AC}/A$			mA
$I_{S2}$	Supply current 24V-supply	$250+170 \cdot f_s / f_{smax} + 2,6 \cdot I_{AC}/A$			mA
$t_{interlock-driver}$	Interlock-time	2,3			μs
<b>SKiiPPACK protection</b>					
$I_{TRIPSC}$	Short circuit protection	250			A
$I_{TRIPLG}$	Ground fault protection	58			A
$T_{TRIP}$	Over-temp. protection	115			°C
$U_{DCTRIP}$ <sup>9)</sup>	$U_{DC}$ -protection	410			V
<b>Mechanical Data</b>					
M1	DC terminals, SI Units	4	–	6	Nm
M2	AC terminals, SI Units	8	–	10	Nm

## SKiiPPACK®

### SK integrated intelligent Power PACK

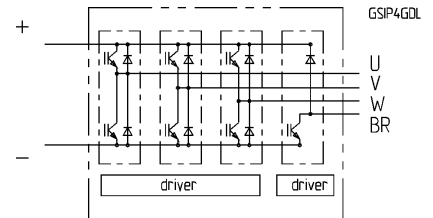
### 3-phase bridge with brake chopper

### SKiiP

### 202 GDL 061 - 457 CTV <sup>7,9)</sup>

### Preliminary Data

### Case S5



### Features

- Short circuit protection, due to evaluation of current sensor signals
- Isolated power supply
- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Over-temperature protection

- <sup>1)</sup>  $T_{heatsink} = 25$  °C, unless otherwise specified
- <sup>2)</sup> CAL = Controlled Axial Lifetime Technology (soft and fast) without driver
- <sup>3)</sup> Driver input to DC link / AC output to DC link / AC output to heatsink
- <sup>4)</sup> with Semikron-DC link (low inductance)
- <sup>5)</sup> other heatsinks on request
- <sup>6)</sup> C - Integrated current sensors
- <sup>7)</sup> T - Temperature protection
- <sup>8)</sup> V - 15 V or 24 V power supply
- <sup>9)</sup> options available for driver:  
U - DC link voltage sense  
F – Fiber optic connector
- <sup>10)</sup> “s” referenced to temperature sensor
- <sup>11)</sup> NPT-technology with homogeneous current-distribution

## SKiiP Brake-chopper

Absolute Maximum Ratings		Values	Units
Symbol	Conditions <sup>1)</sup>		
V <sub>isol</sub> <sup>4)</sup>	AC, 1min	2500	V
T <sub>op</sub> , T <sub>stg</sub>	Operating / stor. temperature	-25...+85	°C
IGBT and Inverse Diode			
V <sub>CES</sub>		600	V
V <sub>CC</sub> <sup>5)</sup>	Operating DC link voltage	400	V
I <sub>C</sub>	IGBT	200	A
T <sub>j</sub> <sup>3)</sup>	IGBT + Diode	-40...+150	°C
I <sub>F</sub>	Diode	200	A
I <sub>FM</sub>	Diode, t <sub>p</sub> < 1 ms	400	A
I <sub>FSM</sub>	Diode, T <sub>j</sub> = 150 °C, 10ms; sin	3000	A
I <sup>2</sup> t (Diode)	Diode, T <sub>j</sub> = 150 °C, 10ms	45	kAs <sup>2</sup>
Driver			
V <sub>S1</sub>	Stabilized Power Supply	18	V
V <sub>S2</sub>	Non-stabilized Power Supply	30	V
f <sub>smax</sub>	Switching frequency	5	kHz
dV/dt	Primary to secondary side	50	kV/μs

Characteristics		min.	typ.	max.	Units
Symbol	Conditions <sup>1)</sup>				
IGBT <sup>11)</sup>					
V <sub>(BR)CES</sub>	Driver without supply	≥V <sub>CES</sub>	–	–	V
I <sub>CES</sub>	V <sub>GE</sub> = 0, T <sub>j</sub> = 25 °C	–	–	0,4	mA
	V <sub>CE</sub> = V <sub>CES</sub> T <sub>j</sub> = 125 °C	–	4,5	–	mA
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	–	–	0,94	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	–	–	6,4	mΩ
V <sub>Cesat</sub>	I <sub>C</sub> = 200A, T <sub>j</sub> = 125 °C	–	–	2,2	V
V <sub>Cesat</sub>	I <sub>C</sub> = 200A, T <sub>j</sub> = 25 °C	–	–	2,65	V
E <sub>on</sub> + E <sub>off</sub>	V <sub>CC</sub> =300/400V, I <sub>C</sub> =200A T <sub>j</sub> = 125 °C	–	–	18/25	mJ
C <sub>CHC</sub>	per SKiiP, AC side	–	0,8	–	nF
L <sub>CE</sub>	Top, Bottom	–	15	–	nH
Inverse Diode <sup>2)</sup>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 200A; T <sub>j</sub> = 125 °C	–	–	1,67	V
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 200A T <sub>j</sub> = 25 °C	–	–	1,75	V
E <sub>on</sub> + E <sub>off</sub>	I <sub>F</sub> = 200A; T <sub>j</sub> = 125 °C	–	–	6	mJ
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	–	–	0,78	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	–	–	3,3	mΩ
Thermal Characteristics					
R <sub>thjs</sub> <sup>10)</sup>	per IGBT	–	–	0,150	K/W
R <sub>thjs</sub> <sup>10)</sup>	per Diode	–	–	0,250	K/W
R <sub>thsa</sub> <sup>6,10)</sup>	P16 heatsink; see case S5	–	–	36	K/KW
Driver					
I <sub>S1</sub>	Supply current 15V-supply	67+10*f <sub>s</sub> /f <sub>smax</sub> +0*I <sub>AC</sub> /A			mA
I <sub>S2</sub>	Supply current 24V-supply	67+10*f <sub>s</sub> /f <sub>smax</sub> +0*I <sub>AC</sub> /A			mA
t <sub>interlock-driver</sub>	Interlock-time	-			μs
SKiiPPACK protection					
I <sub>TRIPSC</sub>	Short circuit protection	Vcesat-protection			A
I <sub>TRIPLG</sub>	Ground fault protection	-			A
T <sub>TRIP</sub>	Over-temp. protection	115			°C
U <sub>DCTRIP</sub> <sup>9)</sup>	U <sub>DC</sub> -protection	410			V
Mechanical Data					
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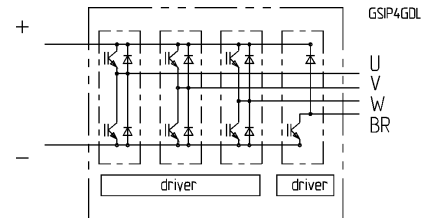
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